L Number	Hits	Search Text	DB	Time stamp
1	32	5676587.pn. 5853604.uref. 5827781.uref.	USPAT; US-PGPUB	2003/07/17 12:02
2	8	5733177.uref.	USPAT; US-PGPUB	2003/07/17 12:03
3	11	(((cmp (chemical near mechanical)) with (copper cu conduct$4 metal))) same (relative near2 (speed velocity))	USPAT; US-PGPUB	2003/07/17 12:03
4	108	((438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative near2 (speed velocity))) and ((cmp (chemical near mechanical)) with (copper cu conduct$4 metal))	USPAT; US-PGPUB	2003/07/17 12:04
5	3	((438/626.ccls. 438/633.ccls. 438/687.ccls.) and (438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.)) and (relative near2 (speed velocity))	USPAT; US-PGPUB	2003/07/17 12:05
6	17	(((cmp (chemical near mechanical)) with (copper cu conduct$4 metal))) same ((relative linear) near2 (speed velocity))	USPAT; US-PGPUB	2003/07/17 12:06
7	21	(((cmp (chemical near mechanical)) with (copper cu conduct$4 metal))) same ((rotat$6 near2 (speed velocity)) rpm rpms) same (change decreas$4 reduc$5)	USPAT; US-PGPUB	2003/07/17 12:07
8	3	(((cmp (chemical near mechanical)) with (copper cu conduct$4 metal))) and (relative near2 (speed velocity))	EPO; JPO; DERWENT; IBM_TDB	2003/07/17 12:07
9	89	(cmp (chemical near mechanical) polish$4) and ((carrier head) same (retain$4 ring) same membrane same (platen pad) same (pressure psi pa)) and (wafer substrate)	USPAT; US-PGPUB	2003/07/17 12:08
10	125	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and (((cmp (chemical near mechanical) polish$4) with (copper cu conduct$4 metal)) and ((carrier head) same (retain$4 ring membrane) same (platen pad) same (pressure psi pa)) and (wafer substrate))	USPAT; US-PGPUB	2003/07/17 12:08
11	126	((cmp (chemical near mechanical) polish$4) and ((carrier head) same (retain$4 ring membrane)) and (platen pad)) and (pressure psi pa copper cu metal conduct$4)	EPO; JPO; DERWENT; IBM_TDB	2003/07/17 12:09
12	4	(cmp (chemical near mechanical) polish$4) and (wafer substrate) and ((carrier head) same (platen pad) same (rpm adj second))	USPAT; US-PGPUB	2003/07/17 12:09
13	0	(cmp (chemical near mechanical) polish$4) and (wafer substrate) and ((carrier head) same (platen pad) same ((rpm rotat$6) near accelerat$5))	USPAT; US-PGPUB	2003/07/17 12:09
14	2	(cmp (chemical near mechanical) polish$4) and (wafer substrate) and ((carrier head) same (platen pad) same ((rpm rotat$6) with accelerat$5))	USPAT; US-PGPUB	2003/07/17 12:10
15	30	(cmp (chemical near mechanical) polish$4) and (wafer substrate) and ((carrier head) same (platen pad) same accelerat$5)	USPAT; US-PGPUB	2003/07/17 12:10

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